Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 211810US99	SERIAL NO. 09/911,495
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	AA	4,174,422	11/13/79	Matthews et al.			
	AB	4,523,211	06/11/85	Morimoto et al.			
	AC	4,661,176	04/28/87	Manasevit			
	AD	4,793,872	12/27/88	Meunier et al.			
	AE	4,855,249	08/08/89	Akasaki et al.			
	AF	4,912,087	03/27/90	Aslam et al.			
	AG	5,173,474	12/22/92	Connell et al.			
	AH	5,358,925	10/25/94	Neville Connell et al.			
	AI	5,393,352	02/28/95	Summerfelt			
	AJ	5,418,216	05/23/95	Fork			
	AK	5,450,812	09/19/95	McKee et al.			
	AL	5,478,653	12/26/95	Guenzer			
	AM	5,482,003	01/09/96	McKee et al.			
	AN	5,514,484	05/07/96	Nashimoto			
	AO	5,588,995	12/31/96	Sheldon			
	AP	5,733,641	03/31/98	Fork et al.			
	AQ	5,830,270	11/03/98	McKee et al.			
	AR	5,912,068	06/15/99	Jia			
	AS	6,020,222	02/01/00	Wollesen			
	AT	6,064,092	05/16/00	Park			
	AU	6,096,584	08/01/00	Ellis-Monaghan et al.			
	AV	6,136,666	10/24/00	So			
	AW	6,174,755	01/16/01	Manning			
	AX	6,180,486	01/30/01	Leobandung et al.			
	AY	3,802,967	04/09/74	Ladany et al.			
	AZ	4,404,265	09/13/83	Manasevit			
	BA	4,482,906	11/13/84	Hovel et al.			
	BB	4,846,926	07/11/89	Kay et al.			
	BC	4,891,091	01/02/90	Shastry			
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	BK	5,670,798	09/23/97	Schetzina			
	BL	5,735,949	04/07/98	Mantl et al.			
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	BO	6,045,626	04/04/00	Yano et al.			
	BP	6,064,078	05/16/00	Northrup et al.			
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	CB	6,113,690	09/05/00	Yu et al.			
	CC	6,143,072	11/07/00	McKee et al.			
	CD	5,155,658	10/13/92	Inam et al.			
	CE	5,248,564	09/28/93	Ramesh			
	CF	5,270,298	12/14/93	Ramesh			
	CG	5,418,389	05/23/95	Watanabe			
	CH	6,055,179	04/25/00	Koganei et al.			
	CI	5,326,721	07/05/94	Summerfelt			
	CJ	5,310,707	05/10/94	Oishi et al.			
	CK	4,999,842	03/12/91	Huang et al.			
	CL	5,874,860	02/23/99	Brunel et al.			
	CM	6,002,375	12/14/99	Corman et al.			
	CN	4,802,182	01/31/89	Thornton et al.			
	CO	4,284,329	08/18/81	Smith et al.			
	CP	4,006,989	02/08/77	Andringa			
	CQ	5,729,641	03/17/98	Chandonnet et al.			
	CR	5,640,267	06/17/97	May et al.			
	CS	5,576,879	11/19/96	Nashimoto			
	CT	5,528,414	06/18/96	Oakley			
	CU	4,802,182	01/31/89	Thornton et al.			
	CV	5,436,759	07/25/95	Dijaii et al.			
	CW	6,128,178	10/03/00	Newns			
	CX	6,121,642	09/19/00	Newns			
	CY	5,926,496	07/20/99	Ho et al.			
	CZ	5,790,583	08/04/98	Ho			
	DA	5,825,799	10/20/98	Ho et al.			
	DB	5,857,049	01/05/99	Beranek et al.			
	DC	6,184,144B1	02/06/01	Lo			
	DD	5,981,400	11/09/99	Lo			
	DE	5,286,985	02/15/94	Taddiken			
	DF	3,766,370	10/16/73	Walther			
	DG	4,777,613	10/11/98	Shahan et al.			
	DH	5,990,495	11/23/99	Ohba			
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	DK	4,896,194	01/23/90	Suzuki			
	DL	5,606,184	02/25/97	Abrokwah, et al.			
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	DN	6,114,996	09/05/00	Nghiem			
	DO	4,882,300	11/21/89	Inoue et al.			
	DP	5,674,366	10/07/97	Hayashi et al.			
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SBG	ED	4,484,332	11/20/84	Hawrylo			
SBG	EE	4,815,084	03/21/89	Scifres et al.			
SBG	EF	5,293,050	03/08/94	Chapple-Sokol et al			
SBG	EG	6,222,654	04/24/01	Frigo			
SBG	EH	5,937,285	08/10/99	Abrokwah et al.			
SBG	EI	5,116,461	05/26/92	Lebby et al.			
SBG	EJ	5,640,267	06/17/97	May et al.			
SBG	EK	5,442,191	08/15/95	Ma			
SBG	EL	6,008,762	12/28/99	Nghiem			
SBG	EM	5,444,016	08/22/95	Abrokwah, et al.			
SBG	EN	5,614,739	03/25/97	Abrokwah et al.			
SBG	EO	5,480,829	01/02/96	Abrokwah, et al.			
SBG	EP	5,144,409	09/01/92	Ma			
SBG	EQ	6,058,131	05/02/00	Pan			
SBG	ER	5,995,359	11/30/99	Klee et al.			
SBG	ES	6,146,906	11/14/00	Inoue et al.			
SBG	ET	6,180,252 B1	01/30/01	Farrell et al.			
SBG	EV	4,876,219	10/24/89	Eshita et al.			
SBG	EW	5,391,515	02/21/95	Kao et al.			
SBG	EX	4,963,508	10/16/90	Umeno et al.			
SBG	EY	5,063,166	11/05/91	Mooney et al.			
SBG	EZ	5,356,831	10/18/94	Calviello et al.			
SBG	FA	5,777,762	07/07/98	Yamamoto			
SBG	FB	5,778,116	07/07/98	Tomich			
SBG	FC	5,127,067	06/30/92	Delcoco et al.			
SBG	FD	5,861,966	01/19/99	Ortel			
SBG	FE	6,137,603	10/24/00	Henmi			
SBG	FF	5,858,814	01/12/99	Goossen et al.			
SBG	FG	5,778,018	07/07/98	Yoshikawa et al.			
SBG	FH	5,764,676	06/09/98	Paoli et al.			
SBG	FI	5,729,394	03/17/98	Sevier et al.			
SBG	FJ	5,883,996	03/16/99	Knapp et al.			
	FK						
	FL						
	FM						
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	FQ						

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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
SBC	AAA	0 250 171	12/23/87	EP	X	
SBC	AAB	0 342 937	11/23/89	EP	X	
SBC	AAC	0 455 526	06/11/91	EP	X	
SBC	AAD	0 602 568	06/22/94	EP	X	
SBC	AAE	0 607 435	07/27/94	EP	X	
SBC	AAF	1 001 468	05/17/00	EP	X	
SBC	AAG	0 514 018	11/19/92	EP	X	
SBC	AAH	0 999 600	05/10/00	EP	X	
SBC	AAI	1 319 311	06/04/70	Great Britain	X	
SBC	AAJ	10-321943	12/04/98	Japan		
SBC	AAK	11-238683	08/31/99	Japan	X	
SBC	AAL	11-260835	09/24/99	Japan w/English Abstract	X	
SBC	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
SBC	AAN	5-48072	02/26/93	Japan w/English Abstract	X	
SBC	AAO	52-88354	07/23/77	Japan	X	
SBC	AAP	54-134554	10/19/79	Japan	X	
SBC	AAQ	55-87424	07/02/80	Japan	X	
SBC	AAR	61-108187	05/26/86	Japan w/English Abstract	X	
SBC	AAS	6-232126	08/19/94	Japan	X	
SBC	AAT	6-291299	10/18/94	Japan w/English Abstract	X	
SBC	AAU	63-34994	02/15/88	Japan w/English Abstract	X	
SBC	AAV	63-131104	06/03/88	Japan w/English Abstract	X	
SBC	AAW	63-198365	08/18/88	Japan	X	
SBC	AAX	63-278629	01/05/90	Japan	X	
SBC	AAY	6-33 4168	12/02/94	Japan	X	
SBC	AAZ	WO 99/63580	12/09/99	WIPO	X	
SBC	BAA	WO 99/14804	03/25/99	WIPO	X	
SBC	BBB	WO 97/45827	12/04/97	WIPO		
SBC	BBC	WO 99/19546	04/22/99	WIPO		
SBC	BBD	WO 00/33363	06/08/00	WIPO		
SBC	BBE	WO 00/48239	08/17/00	WIPO		
SBC	BBF	WO 99/14797	03/25/99	WIPO		
SBC	BBG	GB 2 335 792	09/29/99	Great Britain		
	BBH					
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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT BARBARA F. BARENBURG ET AL	
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